(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
8 January 2004 (08.01.2004)

PCT

(10) International Publication Number
WO 2004/004015 A3

(51) International Patent Classification[7]: H01L 29/786, 21/336

(21) International Application Number: PCT/US2003/020791

(22) International Filing Date: 24 June 2003 (24.06.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
102 29 003.3 28 June 2002 (28.06.2002) DE
10/391,255 18 March 2003 (18.03.2003) US

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(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

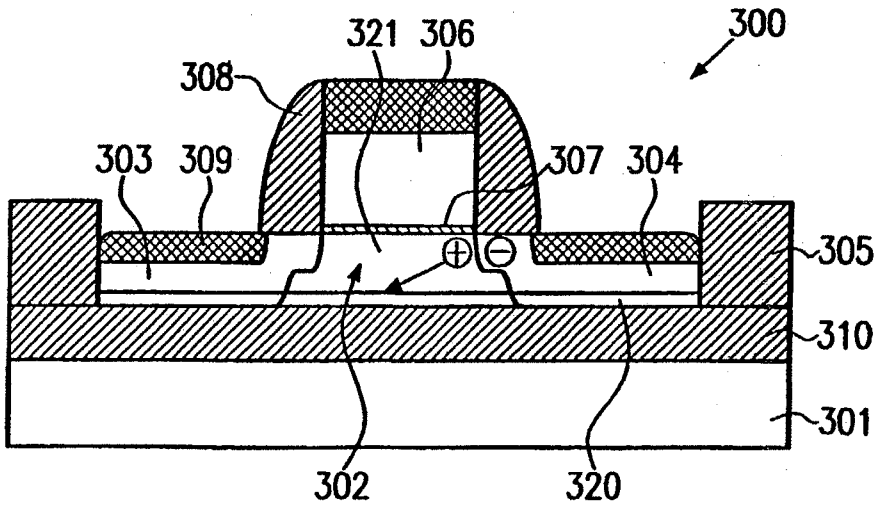
(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report: 8 April 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SOI FIELD EFFECT TRANSISTOR ELEMENT HAVING A RECOMBINATION REGION AND METHOD OF FORMING SAME



(57) Abstract: An SOI transistor element and a method of fabricating the same is disclosed, wherein a high concentration of stationary point defects is created by including a region within the active transistor area that has a slight lattice mismatch. In one particular embodiment, a silicon germanium layer 320 is provided in the active area having a high concentration of point defects due to relaxing the strain of the silicon germanium layer upon heat treating the transistor element. Due to the point defects, the recombination rate is significantly increased, thereby reducing the number of charged carriers stored in the active area.

WO 2004/004015 A3

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(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
8 January 2004 (08.01.2004)

PCT

(10) International Publication Number
WO 2004/004015 A2

(51) International Patent Classification[7]: H01L 29/786, 21/336

(21) International Application Number: PCT/US2003/020791

(22) International Filing Date: 24 June 2003 (24.06.2003)

(25) Filing Language: English

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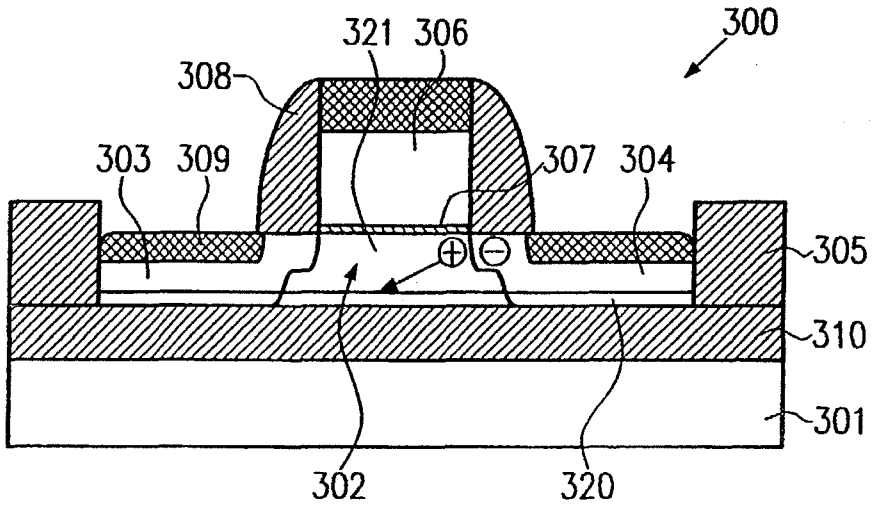
(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

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Published:
— *without international search report and to be republished upon receipt of that report*

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WO 2004/004015 A2